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Kind regards,

Team Nexperia



# PMEG4015EPK

# 40 V, 1.5 A low VF MEGA Schottky barrier rectifier Rev. 2 — 6 March 2012

Product data sheet

## **Product profile**

## 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small SOD1608 (DFN1608D-2) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

#### 1.2 Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 1.5 A
- Reverse voltage: V<sub>R</sub> ≤ 40 V
- Low forward voltage V<sub>F</sub> ≤ 610 mV
- Low reverse current

- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

## 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

#### 1.4 Quick reference data

Table 1. Quick reference data

| Parameter               | Conditions  |   | Min                     | Тур  | Max  | Unit  |
|-------------------------|---|---|-------------------------|--|--|---|
| average forward current | $\delta$ = 0.5; f = 20 kHz; $T_{amb} \le 65$ °C; square wave  | <u>[1]</u>  | -                       | -  | 1.5  | Α   |
|                         | $\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 135 °C; square wave                                       |   | -                       | -  | 1.5  | Α   |
| reverse voltage         | T <sub>j</sub> = 25 °C  |   | -                       | -  | 40   | V   |
| forward voltage         | $I_F$ = 1.5 A; pulsed; $t_p$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_j$ = 25 °C                                   |   | -                       | 540  | 610  | mV  |
| reverse current         | $V_R = 10 \text{ V}; T_j = 25 ^{\circ}\text{C}$   |   | -                       | 1  | 5  | μΑ  |
| reverse recovery time   | $I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$<br>$T_j = 25 ^{\circ}\text{C}$ |   | -                       | 4  | -  | ns  |
|                         | average forward current  reverse voltage forward voltage reverse current                                | $ \begin{array}{ll} \text{average forward} & \delta = 0.5;  f = 20   \text{kHz};  T_{amb} \leq 65  ^{\circ}\text{C}; \\ \text{square wave} \\ \hline \delta = 0.5;  f = 20   \text{kHz};  T_{sp} \leq 135  ^{\circ}\text{C}; \\ \text{square wave} \\ \hline \\ \text{reverse voltage} & T_j = 25  ^{\circ}\text{C} \\ \hline \\ \text{forward voltage} & I_F = 1.5  \text{A};  \text{pulsed};  t_p \leq 300   \mu\text{s};  \delta \leq 0.02; \\ \hline \\ T_j = 25  ^{\circ}\text{C} \\ \hline \\ \text{reverse current} & V_R = 10  \text{V};  T_j = 25  ^{\circ}\text{C} \\ \hline \\ \text{reverse recovery time} & I_R = 0.5  \text{A};  I_{R(meas)} = 0.1  \text{A}; \\ \hline \end{array} $ | average forward current | $\begin{array}{lll} \text{average forward} & \delta = 0.5;  f = 20   \text{kHz};  T_{amb} \leq 65  ^{\circ}\text{C}; & \boxed{11} & - \\ & \text{square wave} & \\ \hline \delta = 0.5;  f = 20   \text{kHz};  T_{sp} \leq 135  ^{\circ}\text{C}; & - \\ & \text{square wave} & \\ \hline \text{reverse voltage} & T_j = 25  ^{\circ}\text{C} & - \\ & \text{forward voltage} & I_F = 1.5  \text{A};  \text{pulsed};  t_p \leq 300   \mu\text{s};  \delta \leq 0.02; & - \\ & T_j = 25  ^{\circ}\text{C} & - \\ \hline \text{reverse current} & V_R = 10  \text{V};  T_j = 25  ^{\circ}\text{C} & - \\ \hline \text{reverse recovery time} & I_R = 0.5  \text{A};  I_{R(meas)} = 0.1  \text{A}; & - \\ \hline \end{array}$ | $ \begin{array}{c} \text{average forward} \\ \text{current} \\ \end{array} \begin{array}{c} \delta = 0.5;  f = 20   \text{kHz};  T_{amb} \leq 65  ^{\circ}\text{C}; \\ \text{square wave} \\ \hline \delta = 0.5;  f = 20   \text{kHz};  T_{sp} \leq 135  ^{\circ}\text{C}; \\ \text{square wave} \\ \end{array} \begin{array}{c} - \\ \text{reverse voltage} \\ \hline T_j = 25  ^{\circ}\text{C} \\ \hline \text{forward voltage} \\ \hline T_j = 25  ^{\circ}\text{C} \\ \hline T_j = 25  ^{\circ}\text{C} \\ \hline \text{reverse current} \\ \hline V_R = 10  \text{V};  T_j = 25  ^{\circ}\text{C} \\ \hline \text{reverse recovery time} \\ \hline I_R = 0.5  \text{A};  I_F = 0.5  \text{A};  I_{R(meas)} = 0.1  \text{A}; \\ \hline \end{array} \begin{array}{c} - \\ - \\ - \\ 4 \\ \hline \end{array} $ | $ \begin{array}{c} \text{average forward} \\ \text{current} \\ \end{array} \begin{array}{c} \delta = 0.5;  f = 20   \text{kHz};  T_{amb} \leq 65  ^{\circ}\text{C}; \\ \text{square wave} \\ \hline \delta = 0.5;  f = 20   \text{kHz};  T_{sp} \leq 135  ^{\circ}\text{C}; \\ \text{square wave} \\ \end{array} \begin{array}{c} - \\ - \\ 1.5 \\ \text{square wave} \\ \end{array} $ $ \begin{array}{c} \text{reverse voltage} \\ \text{If } = 25  ^{\circ}\text{C} \\ \text{If } = 1.5  \text{A; pulsed; } t_p \leq 300   \mu\text{s; } \delta \leq 0.02; \\ \text{Tight } = 25  ^{\circ}\text{C} \\ \text{reverse current} \\ \text{If } = 1.5  \text{A; pulsed; } t_p \leq 300   \mu\text{s; } \delta \leq 0.02; \\ \text{If } = 25  ^{\circ}\text{C} \\ \text{reverse recovery time} \\ \text{If } = 0.5  \text{A; } I_{R(meas)} = 0.1  \text{A; } \\ \end{array} \begin{array}{c} - \\ - \\ - \\ - \\ - \\ - \\ - \\ - \\ - \\ - $ |

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



## 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline   | Graphic symbol               |
|-----|--------|-------------|----------------------|------------------------------|
| 1   | K      | cathode[1]  |                      | . 54 .                       |
| 2   | Α      | anode       | 1 2                  | 1 <del>    2</del><br>sym001 |
|     |        |             | Transparent top view |                              |
|     |        |             | SOD1608 (DFN1608D-2  | 2)                           |

<sup>[1]</sup> The marking bar indicates the cathode.

## 3. Ordering information

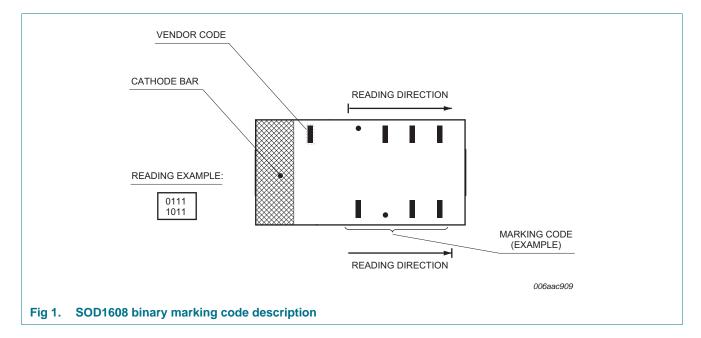
Table 3. Ordering information

| Type number | Package    |   |         |
|-------------|------------|---|---------|
|             | Name       | Description                                       | Version |
| PMEG4015EPK | DFN1608D-2 | Leadless ultra small plastic package; 2 terminals | SOD1608 |

## 4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMEG4015EPK | 0110 0000    |



## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                           | Conditions   |            | Min | Max  | Unit |
|--------------------|-------------------------------------|--|------------|-----|------|------|
| $V_R$              | reverse voltage                     | T <sub>j</sub> = 25 °C   |            | -   | 40   | V    |
| I <sub>F</sub>     | forward current                     | T <sub>sp</sub> ≤ 130 °C   |            | -   | 2.1  | Α    |
| I <sub>F(AV)</sub> | average forward current             | $\delta$ = 0.5; f = 20 kHz; square wave;<br>T <sub>amb</sub> ≤ 65 °C   | <u>[1]</u> | -   | 1.5  | Α    |
|                    |                                     | $\delta$ = 0.5; f = 20 kHz; square wave;<br>T <sub>sp</sub> ≤ 135 °C   |            | -   | 1.5  | Α    |
| I <sub>FRM</sub>   | repetitive peak forward current     | $t_p \le 1 \text{ ms}; \delta \le 0.25$                                |            | -   | 4    | Α    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p = 8 \text{ ms}; T_{j(init)} = 25 \text{ °C}; \text{ square wave}$ |            | -   | 5    | Α    |
| P <sub>tot</sub>   | total power dissipation             | T <sub>amb</sub> ≤ 25 °C   | [2][3]     | -   | 415  | mW   |
|                    |                                     |  | [4][3]     | -   | 895  | mW   |
|                    |                                     |  | [1][3]     | -   | 1565 | mW   |
| Tj                 | junction temperature                |  |            | -   | 150  | °C   |
| T <sub>amb</sub>   | ambient temperature                 |  |            | -55 | 150  | °C   |
| T <sub>stg</sub>   | storage temperature                 |  |            | -65 | 150  | °C   |
|                    |                                     |  |            |     |      |      |

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

## 6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter  | Conditions |            | Min | Тур | Max | Unit |
|----------------|--|------------|------------|-----|-----|-----|------|
| ing a)         | thermal resistance                                     | [1][4][3   | [1][2][3]  | -   | -   | 300 | K/W  |
|                | from junction to                                       |            | [1][4][3]  | -   | -   | 140 | K/W  |
|                | amblem   |            | [1][5][3]  | -   | -   | 80  | K/W  |
| $R_{th(j-sp)}$ | thermal resistance<br>from junction to solder<br>point |            | <u>[6]</u> | -   | -   | 20  | K/W  |

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub>are a significant part of the total power losses.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Reflow soldering is the only recommended soldering method.

<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Reflow soldering is the only recommended soldering method.

<sup>[4]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[5]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[6]</sup> Soldering point of cathode tab.

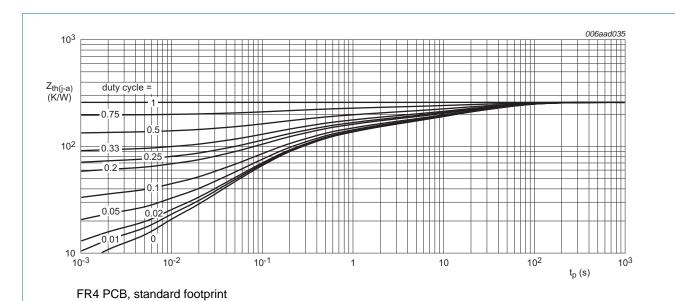
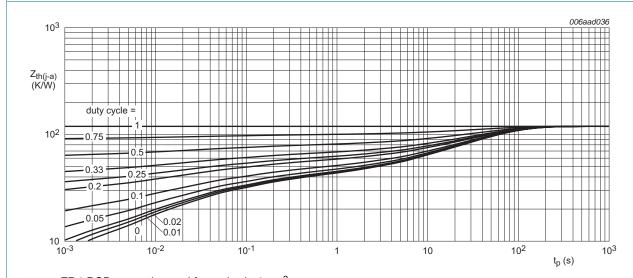
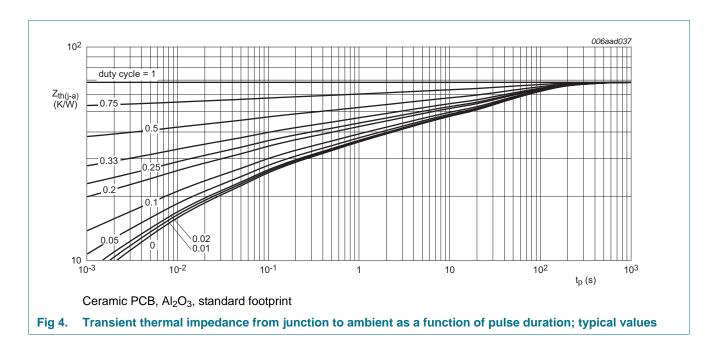


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

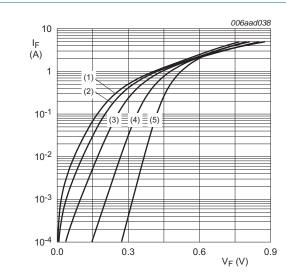
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 7. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter                                 | Conditions  | Min | Тур | Max | Unit |
|--------------------------------|---|---|-----|-----|-----|------|
| $V_{F}$                        | forward voltage                           | $I_F$ = 100 mA; pulsed; $t_p \le 300 \ \mu s$ ;<br>$\delta \le 0.02$ ; $T_j = 25 \ ^{\circ}C$           | -   | 330 | 380 | mV   |
|                                |   | $I_F$ = 500 mA; pulsed; $t_p \le 300 \ \mu s$ ;<br>$\delta \le 0.02$ ; $T_j$ = 25 °C                    | -   | 415 | 480 | mV   |
|                                |   | $I_F$ = 1 A; pulsed; $t_p \le 300$ μs; $\overline{o} \le 0.02$ ; $T_j$ = 25 °C                          | -   | 490 | 550 | mV   |
|                                |   | $I_F$ = 1.5 A; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02; $T_j$ = 25 °C                                  | -   | 540 | 610 | mV   |
| I <sub>R</sub> reverse current | $V_R = 10 \text{ V}; T_j = 25 \text{ °C}$ | -   | 1   | 5   | μΑ  |      |
|                                |   | V <sub>R</sub> = 40 V; T <sub>j</sub> = 25 °C   | -   | 8   | 30  | μA   |
| C <sub>d</sub>                 | diode capacitance                         | $V_R = 1 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$   | -   | 75  | 90  | pF   |
|                                |   | $V_R = 10 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$  | -   | 30  | 40  | pF   |
| t <sub>rr</sub>                | reverse recovery time                     | $I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$<br>$T_j = 25 ^{\circ}\text{C}$ | -   | 4   | -   | ns   |
| $V_{FRM}$                      | peak forward recovery voltage             | $I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$     | -   | 440 | -   | mV   |
|                                |   |   |     |     |     |      |



- (1)  $T_i = 150 \, ^{\circ}C$
- (2)  $T_i = 125 \, ^{\circ}C$
- (3)  $T_i = 85 \, ^{\circ}C$
- (4)  $T_j = 25 \, ^{\circ}C$
- (5) T<sub>i</sub> = −40 °C

Fig 5. Forward current as a function of forward voltage; typical values

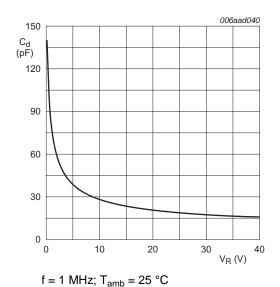
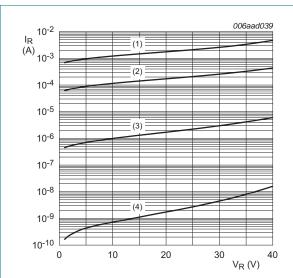
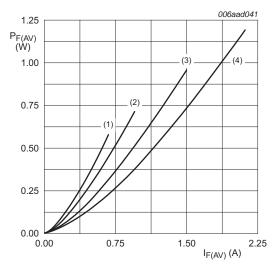


Fig 7. Diode capacitance as a function of reverse voltage; typical values



- (1)  $T_i = 125 \, ^{\circ}C$
- (2)  $T_i = 85 \, ^{\circ}C$
- (3)  $T_j = 25 \, ^{\circ}C$
- (4)  $T_i = -40 \, ^{\circ}C$

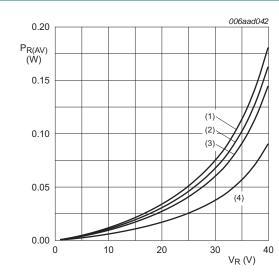
Fig 6. Reverse current as a function of reverse voltage; typical values



T<sub>i</sub> = 150 °C

- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

Fig 8. Average forward power dissipation as a function of average forward current; typical values



T<sub>i</sub> = 125 °C

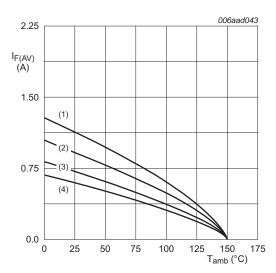
(1)  $\delta = 1$ 

(2)  $\delta = 0.9$ 

(3)  $\delta = 0.8$ 

(4)  $\delta = 0.5$ 

Fig 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T<sub>i</sub> = 150 °C

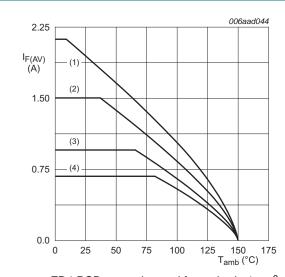
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1  $\mbox{cm}^2$ 

T<sub>i</sub> = 150 °C

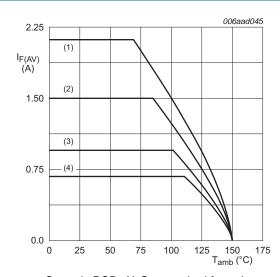
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

 $T_i = 150 \,^{\circ}\text{C}$ 

(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

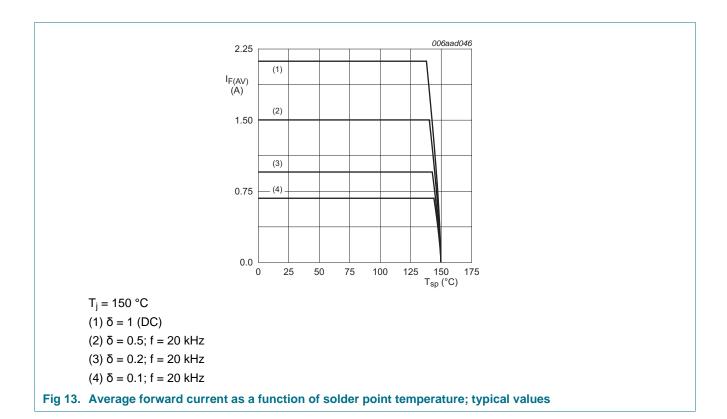
(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 12. Average forward current as a function of ambient temperature; typical values

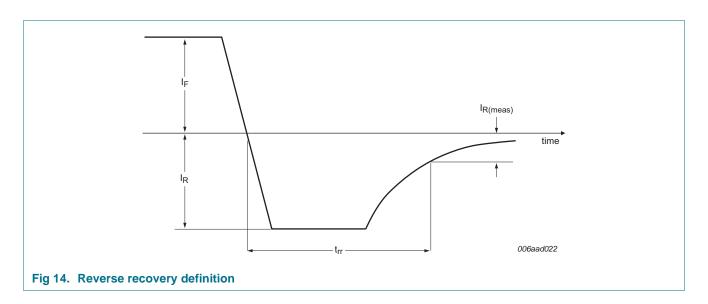
PMEG4015EPK

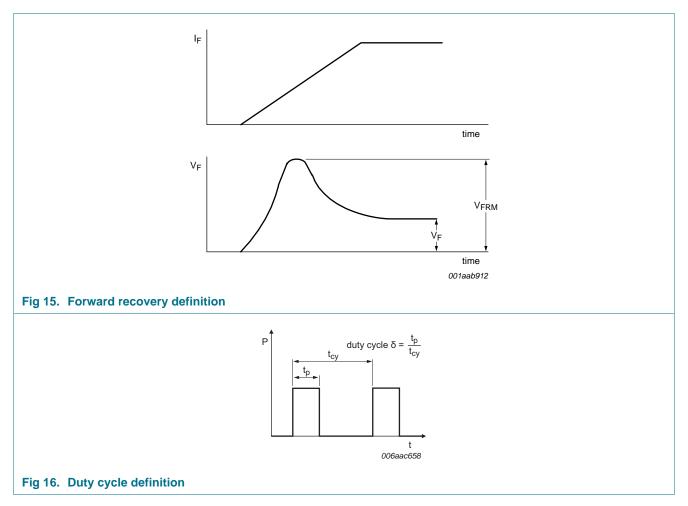
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## 8. Test information



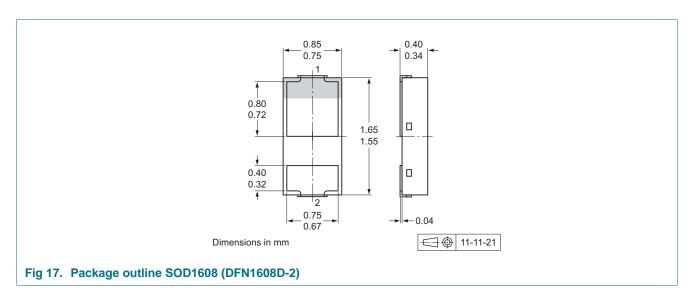


The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

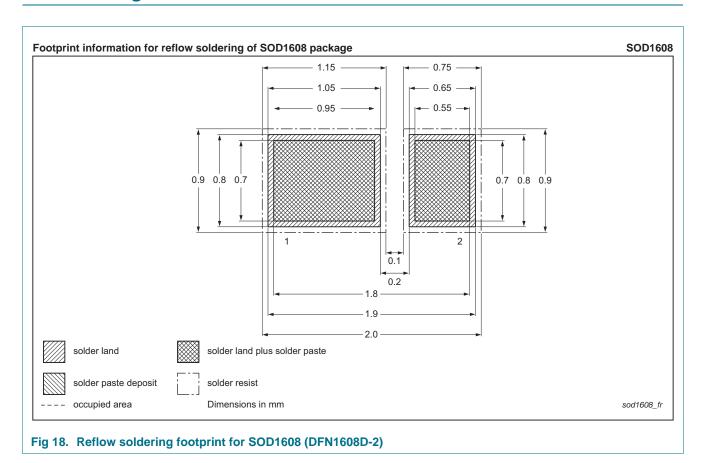
## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Soldering





## 11. Revision history

## Table 8. Revision history

| Document ID     | Release date                       | Data sheet status  | Change notice | Supersedes      |
|-----------------|------------------------------------|--------------------|---------------|-----------------|
| PMEG4015EPK v.2 | 20120306                           | Product data sheet | -             | PMEG4015EPK v.1 |
| Modifications:  | <ul> <li>Fig 14. and 15</li> </ul> | corrected title    |               |                 |
| PMEG4015EPK v.1 | 20120302                           | Product data sheet | -             | -               |

## 12. Legal information

#### 12.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URLhttp://www.nxp.com.

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PMEG4015EPK

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## PMEG4015EPK

#### 40 V, 1.5 A low VF MEGA Schottky barrier rectifier

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## 13. Contact information

For more information, please visit:http://www.nxp.com

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